

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

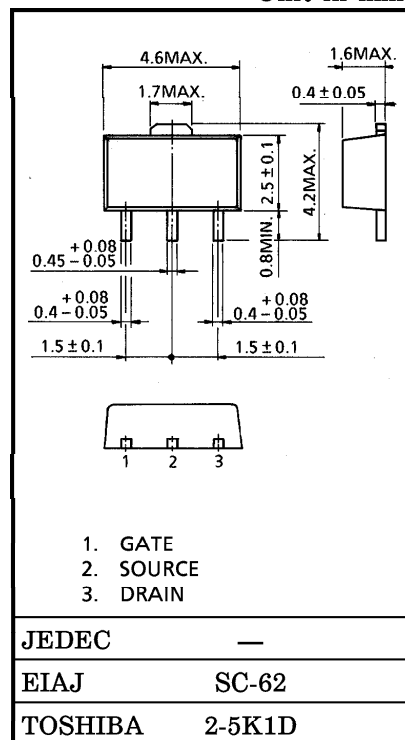
2SK2854

UHF BAND AMPLIFIER APPLICATION

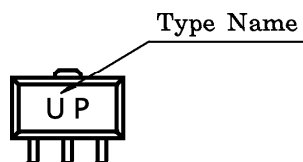
Unit in mm

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V _{DSS}	10	V
Gate-Source Voltage	V _{GS}	±6	V
Drain Current	I _D	0.5	A
Drain Power Dissipation	P _D	0.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



MARKING



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Power	P _O	V _D S = 6V, f = 849MHz P _i = 13dBmW	23	—	—	dBmW
Drain Efficiency	η _D	V _D S = 6V, f = 849MHz P _i = 13dBmW, P _O = 23dBmW	40	—	—	%
Drain-Source Breakdown Voltage	V _(BR) DSS	V _{GS} = 0, I _D = 1μA	10	—	—	V
Drain Cut-off Current	I _{DSS}	V _D S = 6V, V _{GS} = 0	—	—	100	nA
Threshold Voltage	V _{th}	V _D S = 6V, I _D = 250μA	1.0	1.4	1.8	V
Gate-Source Leakage Current	I _{GSS}	V _{GS} = 6V, V _D S = 0	—	—	±100	nA

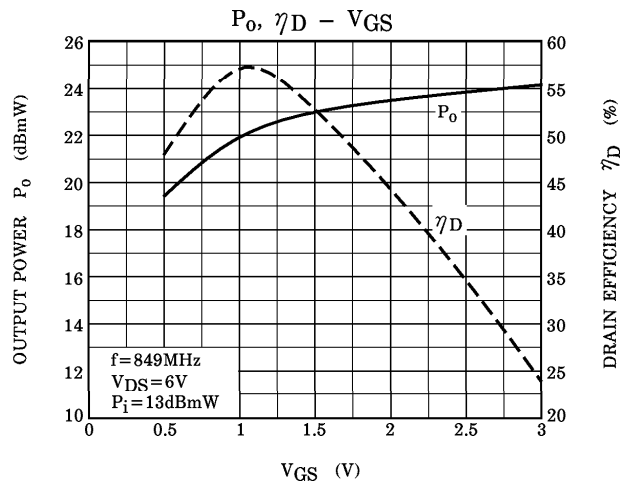
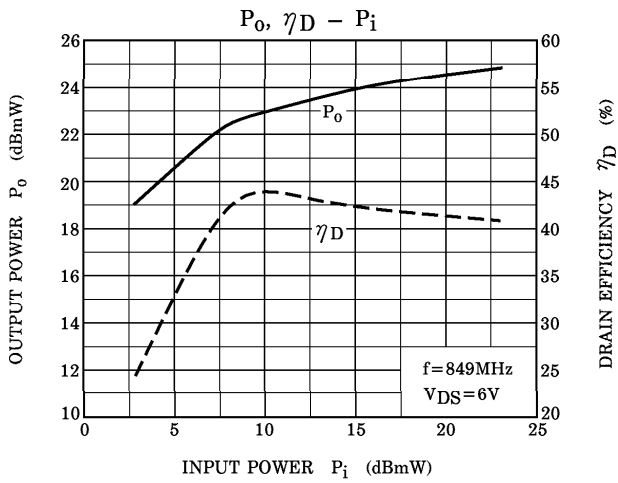
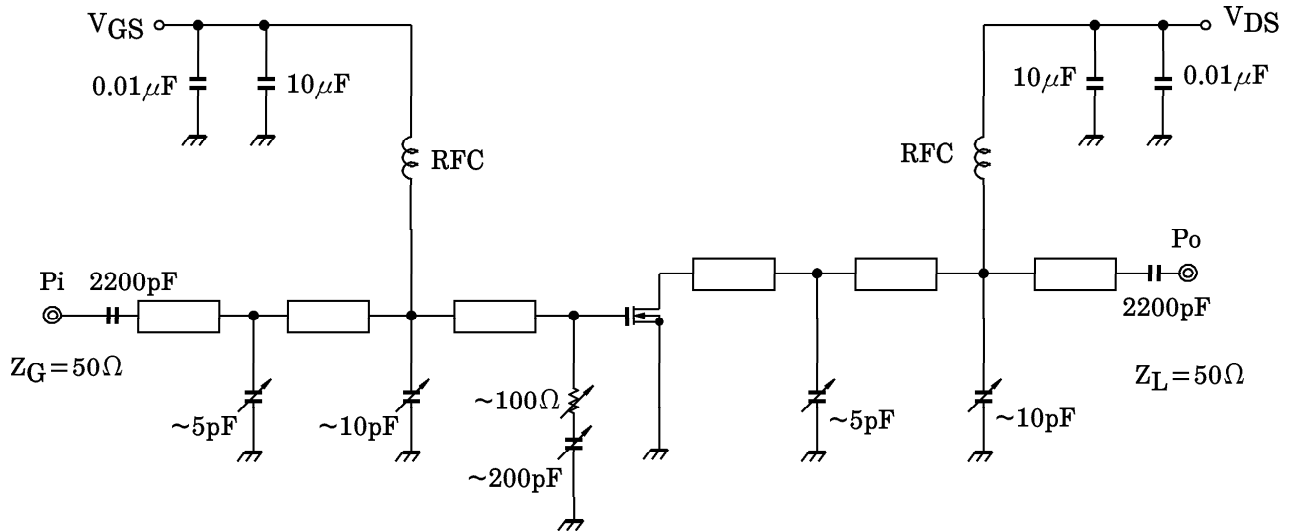
CAUTION

This transistor is the electrostatic sensitive device.
Please handle with caution.

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RF OUTPUT POWER TEST FIXTURE



CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.